

PerFET™ Power Transistor

FEATURES

- Ultra-low On-resistance
- Wettable Flank leads for Enhanced AOI
- 100% UIS and Rg tested
- 175°C Operating Junction Temperature
- RoHS Compliant
- Halogen-Free according to IEC 61249-2-21

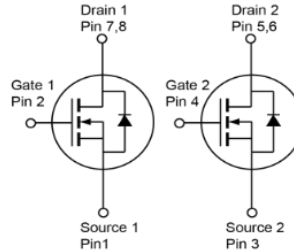
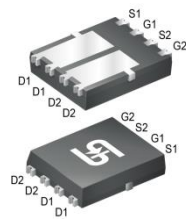
APPLICATIONS

- DC-DC Converters
- Solenoid and Motor Drivers
- Load Switch

PRODUCT SUMMARY			
PARAMETER		VALUE	UNIT
V_{DS}		40	V
$R_{DS(on)}$ (max)	$V_{GS} = 10V$	7.6	mΩ
	$V_{GS} = 7V$	9.1	
Q_g	$V_{GS} = 10V$	19	nC



PDFN56U Dual



Note: MSL 1 (Moisture Sensitivity Level) per J-STD-020

ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$ unless otherwise noted)				
PARAMETER		SYMBOL	LIMIT	UNIT
Drain-Source Voltage		V_{DS}	40	V
Gate-Source Voltage		V_{GS}	± 20	V
Continuous Drain Current, Silicon limited	$T_C = 25^\circ\text{C}$	I_D	64	A
Continuous Drain Current ^(Note 1)	$T_C = 25^\circ\text{C}$	I_D	34	A
	$T_C = 100^\circ\text{C}$		34	
	$T_A = 25^\circ\text{C}$		15	
Pulsed Drain Current		I_{DM}	136	A
Single Pulse Avalanche Current ^(Note 2)		I_{AS}	17	A
Single Pulse Avalanche Energy ^(Note 2)		E_{AS}	43.6	mJ
Total Power Dissipation	$T_C = 25^\circ\text{C}$	P_D	55.6	W
	$T_C = 125^\circ\text{C}$		18.5	
Operating Junction and Storage Temperature Range		T_J, T_{STG}	-55 to +175	$^\circ\text{C}$

THERMAL RESISTANCE			
PARAMETER	SYMBOL	MAXIMUM	UNIT
Thermal Resistance – Junction to Case	$R_{\theta JC}$	2.7	$^\circ\text{C/W}$
Thermal Resistance – Junction to Ambient	$R_{\theta JA}$	50	$^\circ\text{C/W}$

Note: $R_{\theta JA}$ is the sum of the junction-to-case and case-to-ambient thermal resistances. The case-thermal reference is defined at the solder mounting surface of the drain pins. $R_{\theta JC}$ is guaranteed by design while $R_{\theta CA}$ is determined by the user's board design.

ELECTRICAL CHARACTERISTICS (T _A = 25°C unless otherwise noted)						
PARAMETER	CONDITIONS	SYMBOL	MIN	TYP	MAX	UNIT
Static						
Drain-Source Breakdown Voltage	V _{GS} = 0V, I _D = 1mA	BV _{DSS}	40	--	--	V
Gate Threshold Voltage	V _{GS} = V _{DS} , I _D = 250μA	V _{GS(TH)}	2.4	3	3.6	V
Gate-Source Leakage Current	V _{GS} = ±20V, V _{DS} = 0V	I _{GSS}	--	--	±100	nA
Drain-Source Leakage Current	V _{GS} = 0V, V _{DS} = 40V	I _{DSS}	--	--	1	μA
	V _{GS} = 0V, V _{DS} = 40V T _J = 125°C		--	--	100	
Drain-Source On-State Resistance (Note 3)	V _{GS} = 10V, I _D = 17A	R _{DS(on)}	--	6.5	7.6	mΩ
	V _{GS} = 7V, I _D = 17A		--	7.5	9.1	
Forward Transconductance (Note 3)	V _{DS} = 10V, I _D = 10A	g _{fs}	--	42	--	S
Dynamic						
Total Gate Charge	V _{GS} = 7V, V _{DS} = 20V, I _D = 15A	Q _g	--	13.6	--	nC
Total Gate Charge	V _{GS} = 10V, V _{DS} = 20V, I _D = 15A	Q _g	--	19	--	
Gate-Source Charge		Q _{gs}	--	5.7	--	
Gate-Drain Charge		Q _{gd}	--	3.8	--	
Input Capacitance	V _{GS} = 0V, V _{DS} = 25V, f = 1.0MHz	C _{iss}	--	1217	--	pF
Output Capacitance		C _{oss}	--	235	--	
Reverse Transfer Capacitance		C _{rss}	--	17	--	
Gate Resistance	f = 1.0MHz	R _g	--	1.7	--	Ω
Switching (Note 4)						
Turn-On Delay Time	V _{GS} = 10V, V _{DS} = 20V, I _D = 15A, R _G = 3.3Ω	t _{d(on)}	--	9.9	--	nS
Rise Time		t _r	--	49.3	--	
Turn-Off Delay Time		t _{d(off)}	--	18.2	--	
Fall Time		t _f	--	5	--	
Source-Drain Diode						
Diode Forward Voltage (Note 3)	V _{GS} = 0V, I _S = 17A	V _{SD}	--	--	1.1	V
Reverse Recovery Time	I _S = 15A,	t _{rr}	--	30	--	nS
Reverse Recovery Charge	di/dt = 100A/μs	Q _{rr}	--	23	--	nC

Notes:

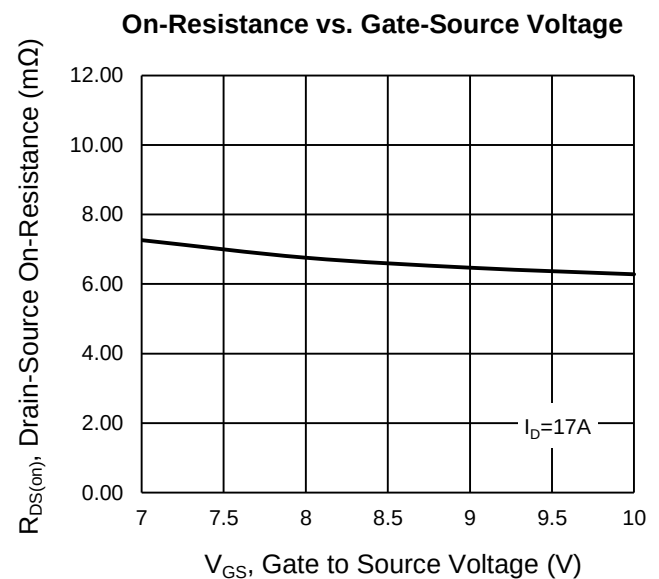
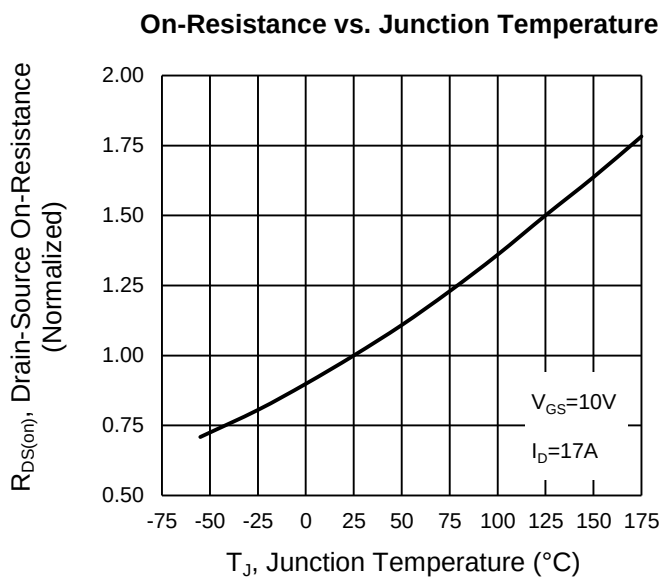
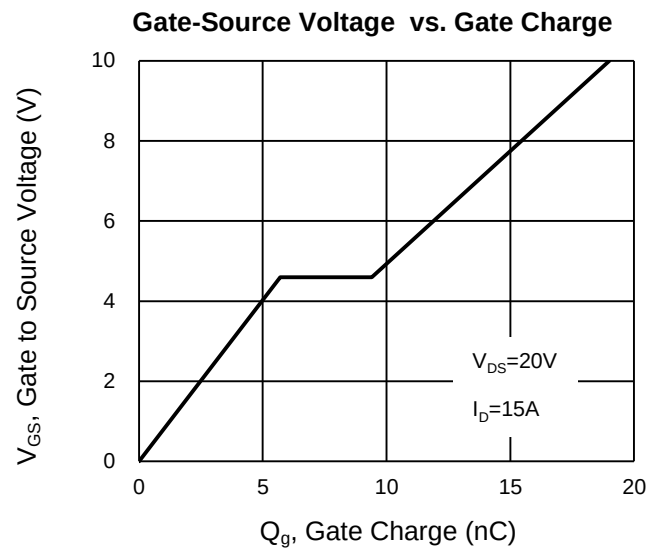
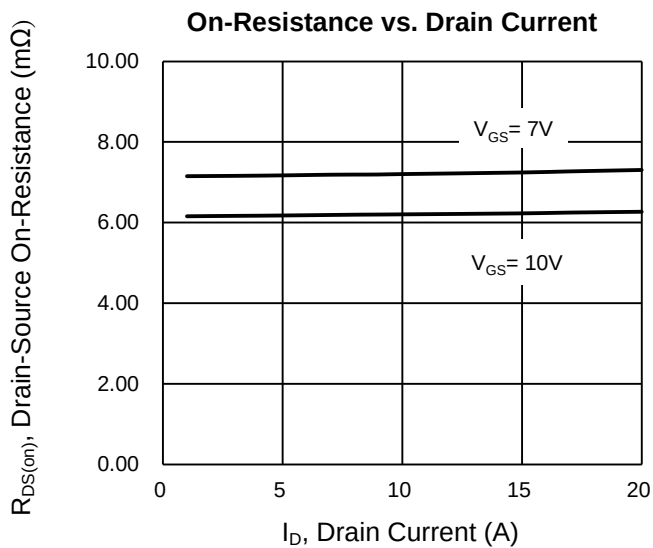
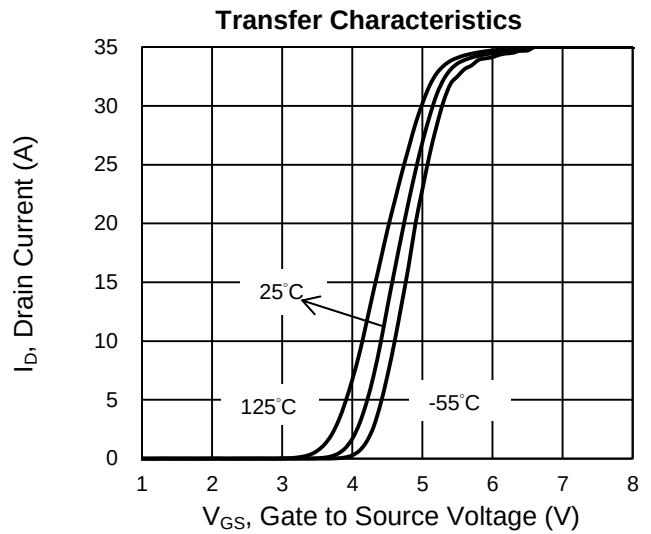
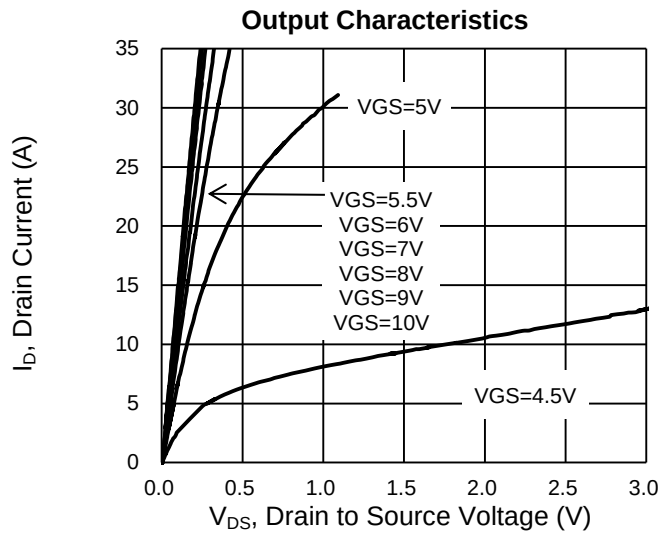
1. Package current limit.
2. $L = 0.3\text{mH}$, $V_{GS} = 10\text{V}$, $R_G = 25\Omega$, Starting $T_J = 25^\circ\text{C}$.
3. Pulse test: Pulse Width $\leq 300\mu\text{s}$, duty cycle $\leq 2\%$.
4. Switching time is essentially independent of operating temperature.

ORDERING INFORMATION

ORDERING CODE	PACKAGE	PACKING
TSM076NH04DCR RLG	PDFN56U Dual	2,500pcs / 13" Reel

CHARACTERISTICS CURVES

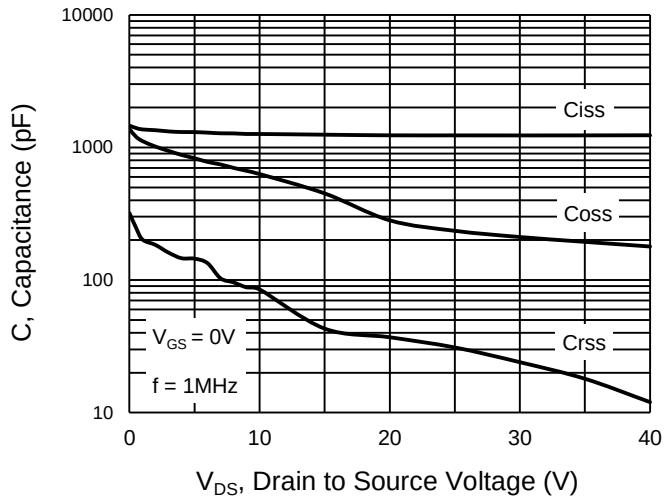
($T_A = 25^\circ\text{C}$ unless otherwise noted)



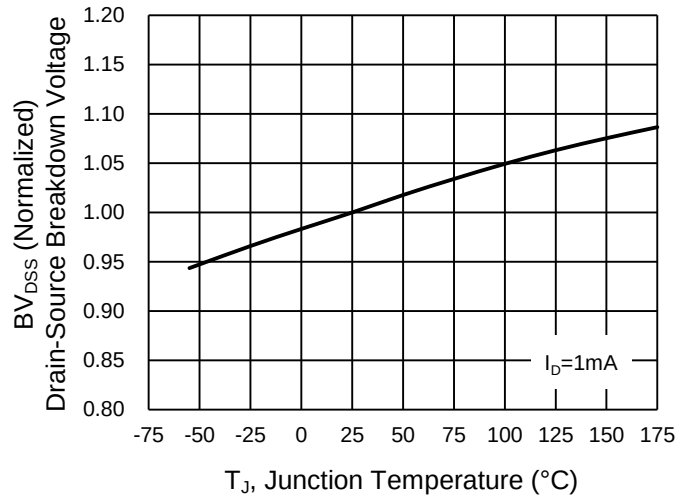
CHARACTERISTICS CURVES

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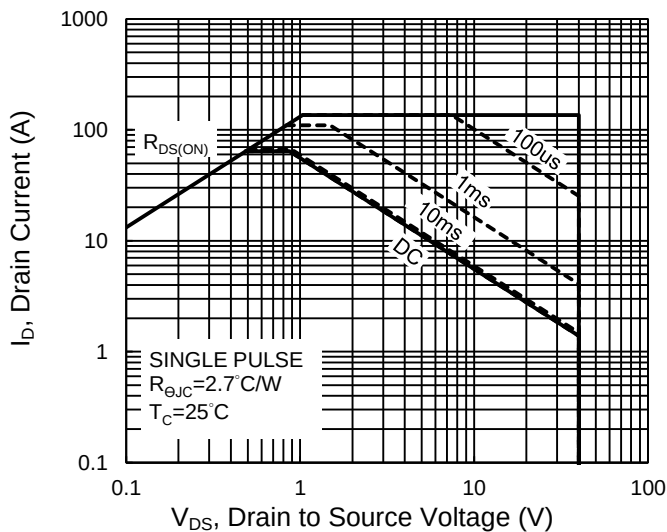
Capacitance vs. Drain-Source Voltage



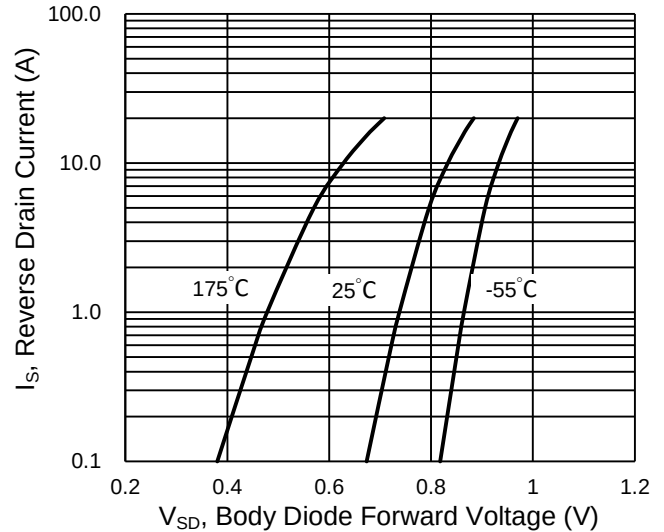
BV_{DSS} vs. Junction Temperature



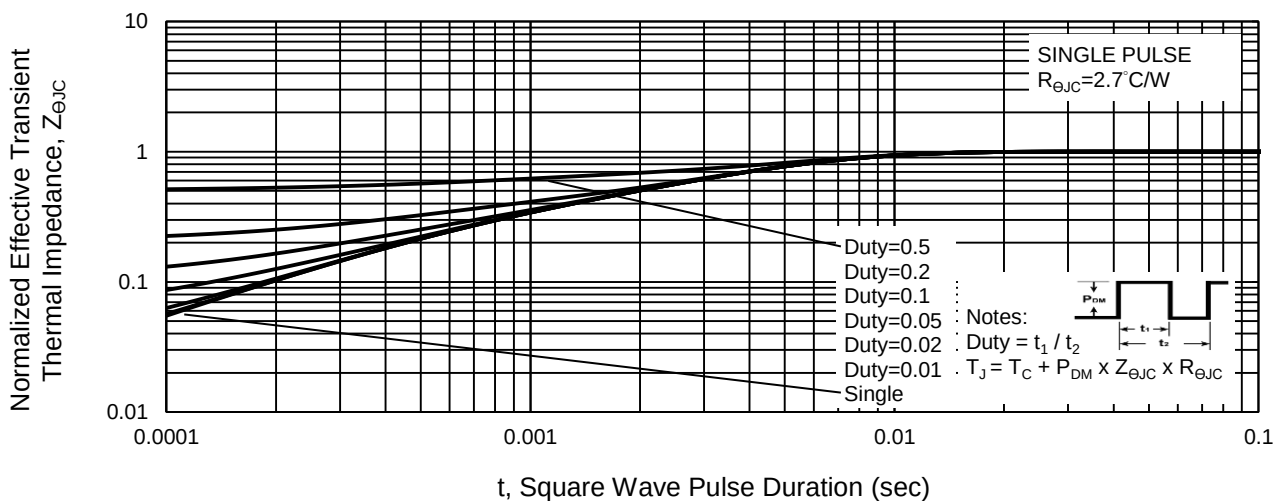
Maximum Safe Operating Area, Junction-to-Case



Source-Drain Diode Forward Current vs. Voltage

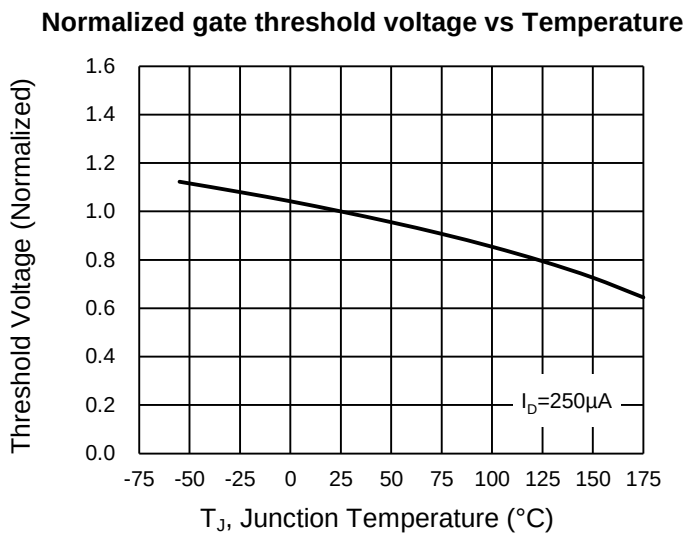
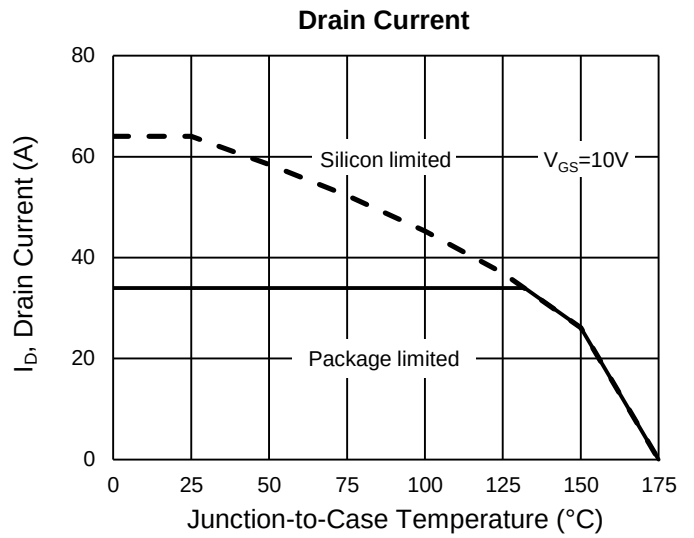
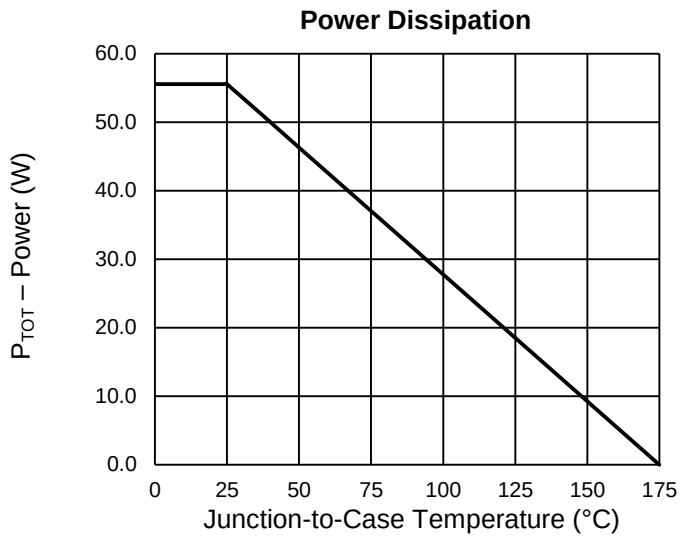


Normalized Thermal Transient Impedance, Junction-to-Case



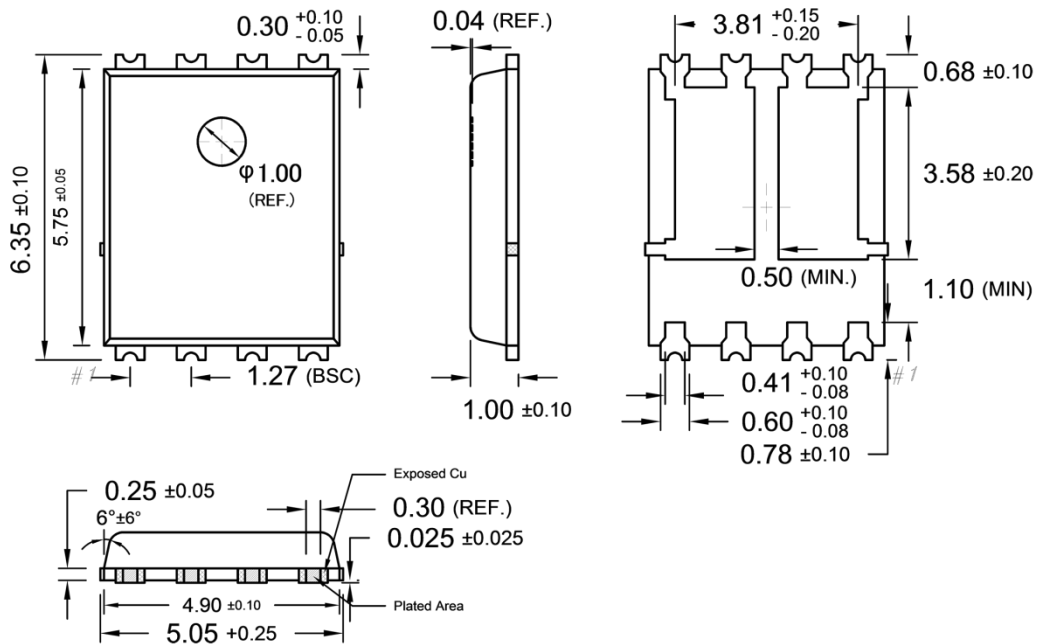
CHARACTERISTICS CURVES

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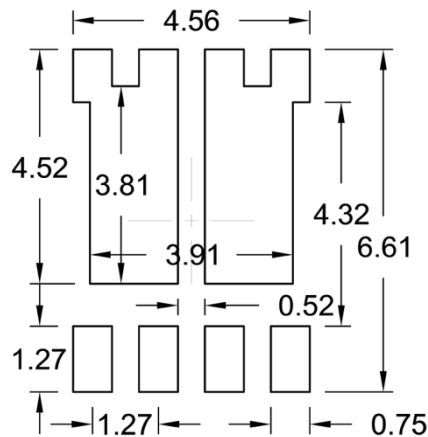


PACKAGE OUTLINE DIMENSIONS (Unit: Millimeters)

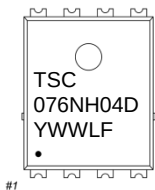
PDFN56U Dual



SUGGESTED PAD LAYOUT (Unit: Millimeters)



MARKING DIAGRAM



- Y** = Year Code
- WW** = Week Code (01~52)
- L** = Lot Code (1~9, A~Z)
- F** = Factory Code

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